

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1848080	semiconductor	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 07:38
S2	15461	semiconductor with island	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:53
S3	173	semiconductor with island with recess	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:53
S4	3	S3 underetching	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:55
S5	92	S3 etching	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:55
S6	0	S5 high adj ohmic material	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:56

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S7	1711	high adj ohm\$ material	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:56
S8	755	S7 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:56
S9	0	S7 S3	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:56
S10	0	S3 high adj ohm\$ material	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:57
S11	31	S7 semiconductor near6 island	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 12:58
S12	755	(high adj ohm\$ material) semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:00

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S13	0	(high adj ohm\$ material) semiconductor with island near15 recess	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:00
S14	25	(high adj ohm\$ material) semiconductor near15 recess	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:04
S15	346	(high adj ohm\$ material) semiconductor etch\$	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:05
S16	15	(high adj ohm\$ material) semiconductor underetch\$	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:07
S17	15	high adj ohm\$ semiconductor underetch\$	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:11
S18	4	"6285057"	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 15:55

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S19	4	"2003045119"	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:15
S20	13	wang hsiao adj lei	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:29
S21	15	"3715232"	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 13:29
S22	41	"5972758"	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/16 15:56
S23	43930	semiconductor with trench	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 07:38
S24	6707	semiconductor with trench with dielectric	US-PGPUB; USPAT; EPO;JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 07:38

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S25	120	semiconductor with trench with dielectric with groove	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 07:46
S26	3	semiconductor with trench with dielectric with groove with high adj conductiv\$	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 08:07
S27	20162	semiconductor with silicon with germanium	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 08:07
S28	15255	semiconductor with (silicon with germanium layer)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 08:08
S29	516	semiconductor with (mixed crystal with silicon with germanium layer)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 08:08
S30	386	semiconductor with (mixed crystal with silicon with germanium layer) with germanium	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 08:08

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S31	3	semiconductor with (mixed crystal with silicon with germanium layer) with trench	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:17
S32	1	semiconductor with (mixed crystal with silicon with germanium layer) with groove	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:43
S33	283	semiconductor with multiple devices with groove	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:44
S34	0	semiconductor with (mixed crystal with silicon with germanium layer) with multiple devices with groove	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:43
S35	64	semiconductor with multiple devices with groove and anisotropic etching	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:45
S36	901649	semiconductor with multiple devices with groove or cavity	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:51

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S37	137	semiconductor with multiple devices with groove and cavity	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	AND	ON	2007/08/17 12:53
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